

**1. Material** Substrate GaAlAs (P Type) Removed  
Epitaxial Layer GaAlAs (N/P Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

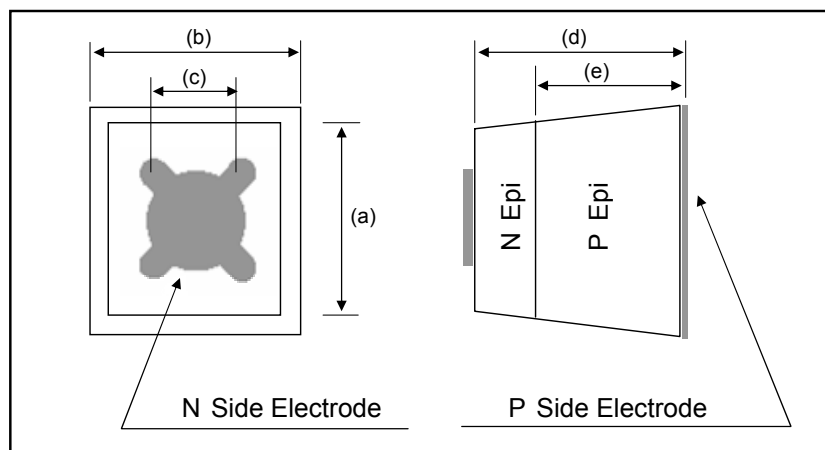
**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.8	2	V	IF=100mA
Reverse Voltage	$V_R$	4			V	IR=10uA
Power	$P_O$		10.25		mW	IF=100mA
Wavelength	$\lambda_P$		880		nm	IF=20mA
	$\Delta\lambda$		80		nm	IF=20mA
Rise Time	$T_r$		700		ns	
Fall Time	$T_f$		400		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

- (a) Emission Area ----- 10.0mil x 10.0mil
- (b) Bottom Area ----- 11.0mil x 11.0mil
- (c) Bonding Pad ----- 110um
- (d) Chip Thickness ----- 10mil
- (e) Junction Height ----- 9.0mil



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